

物理学会2025年春季大会 @ 東京理科大学 野田キャンパス

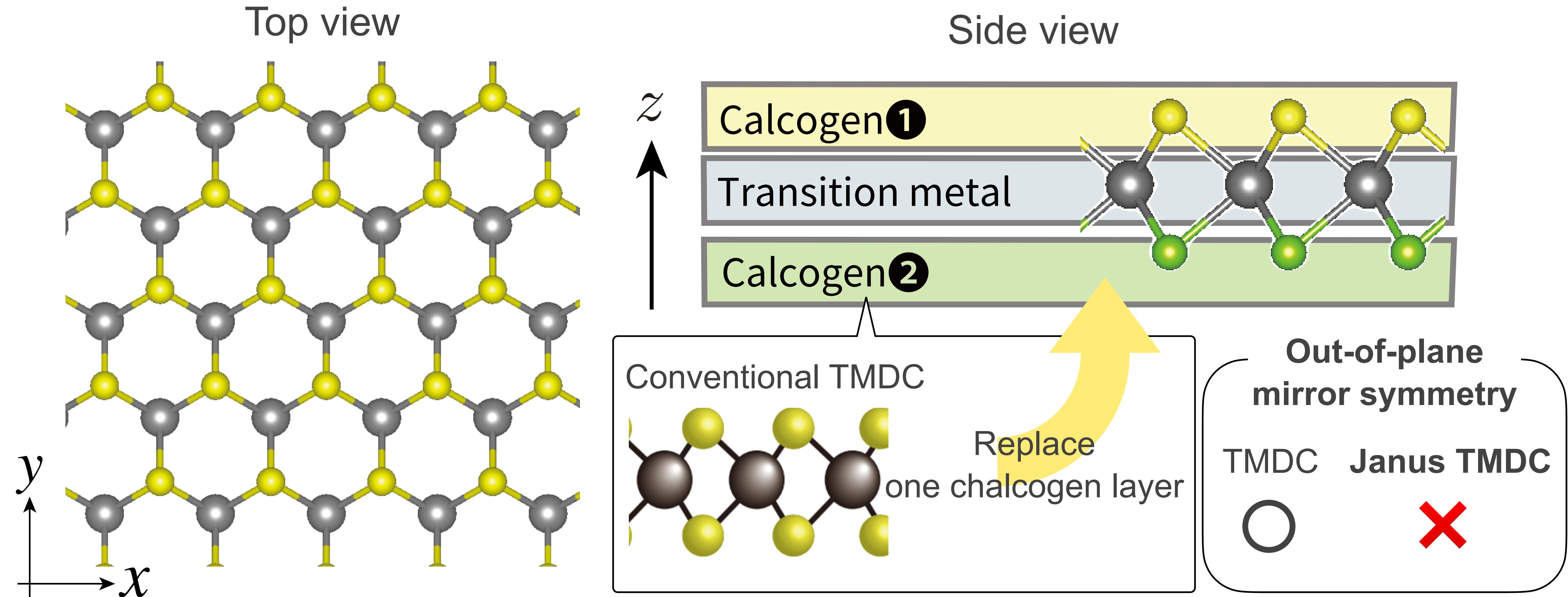
2025/3/20 (木)

講演番号 : 20pD1-4

単層ヤヌス遷移金属ダイカルコゲナイトにおける 光誘起 спин流に関する理論研究

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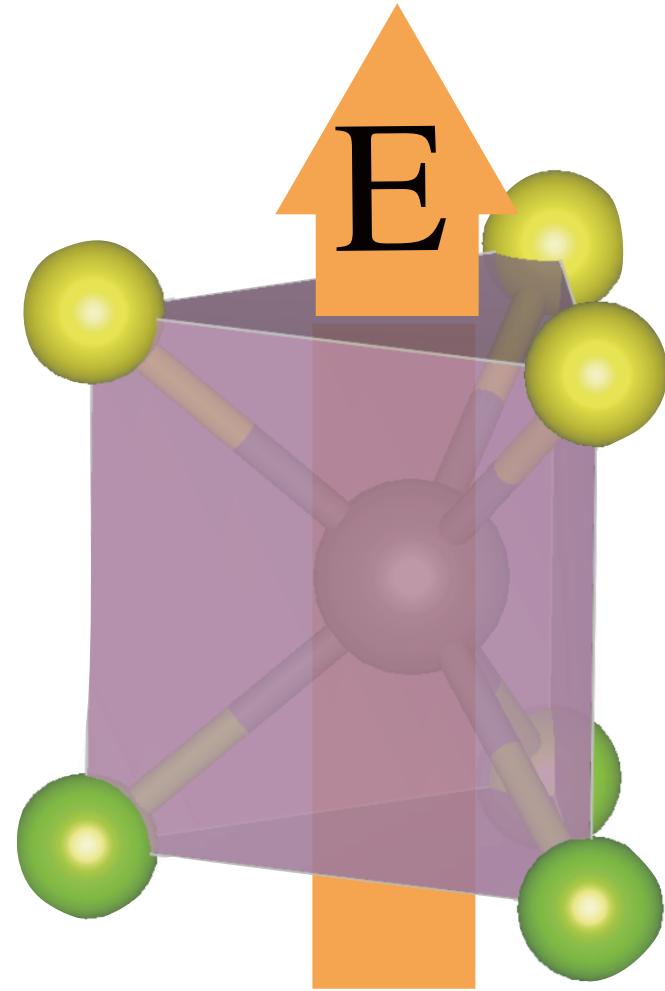
Monolayer Janus transition metal dichalcogenide (Janus TMDC)



- Honeycomb lattice type two-dimensional thin film crystal
- Composed of **transition metal atoms** (1 species) and **chalcogens** (2 species)

Rashba-type spin-orbit coupling (Rashba SOC) in Janus TMDCs

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- Out-of-plane mirror symmetry breaking
- Internal electric field

Janus TMDCs have

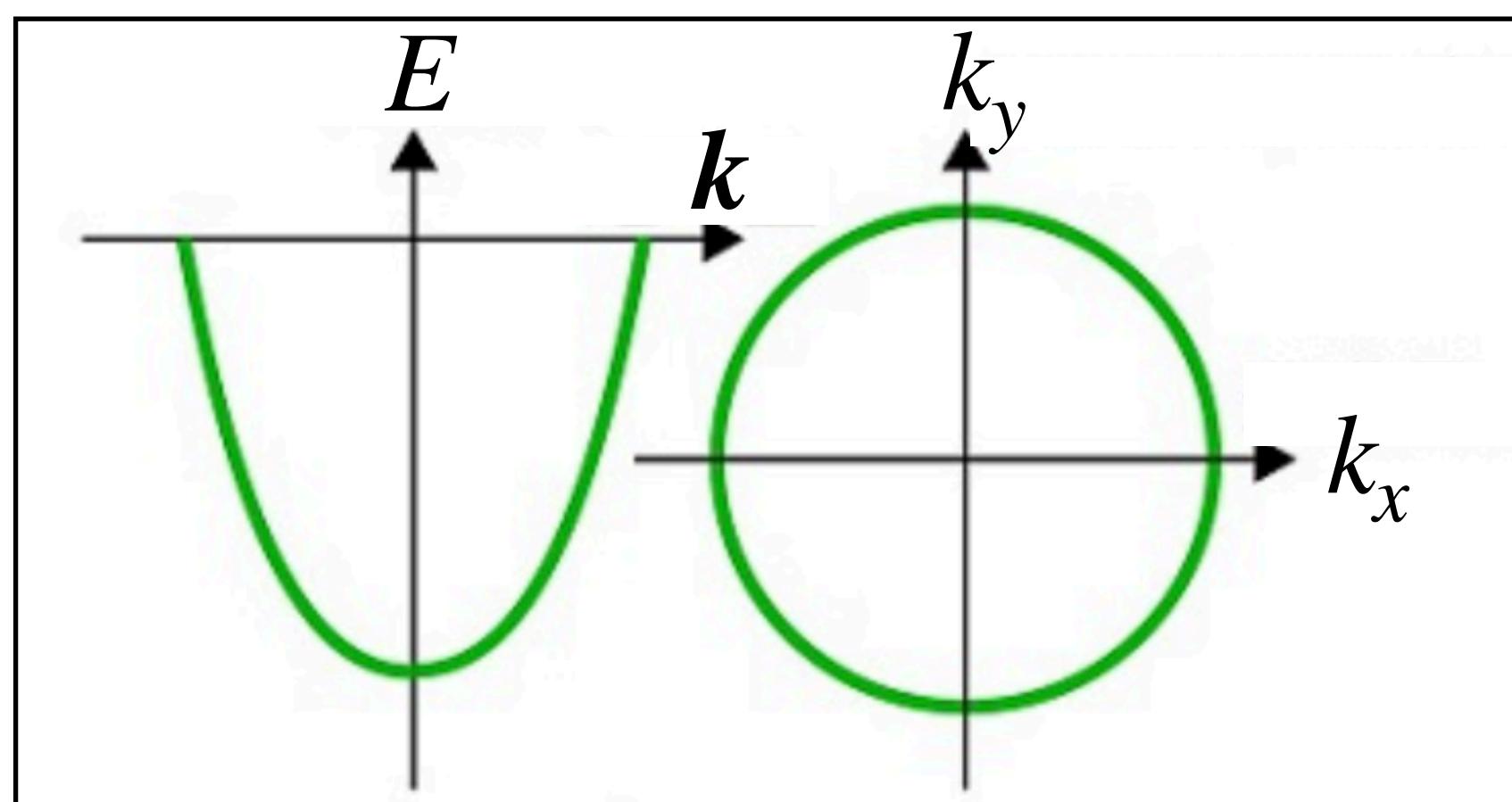
Rashba-type spin-orbit coupling
without external electric field

Topic of study

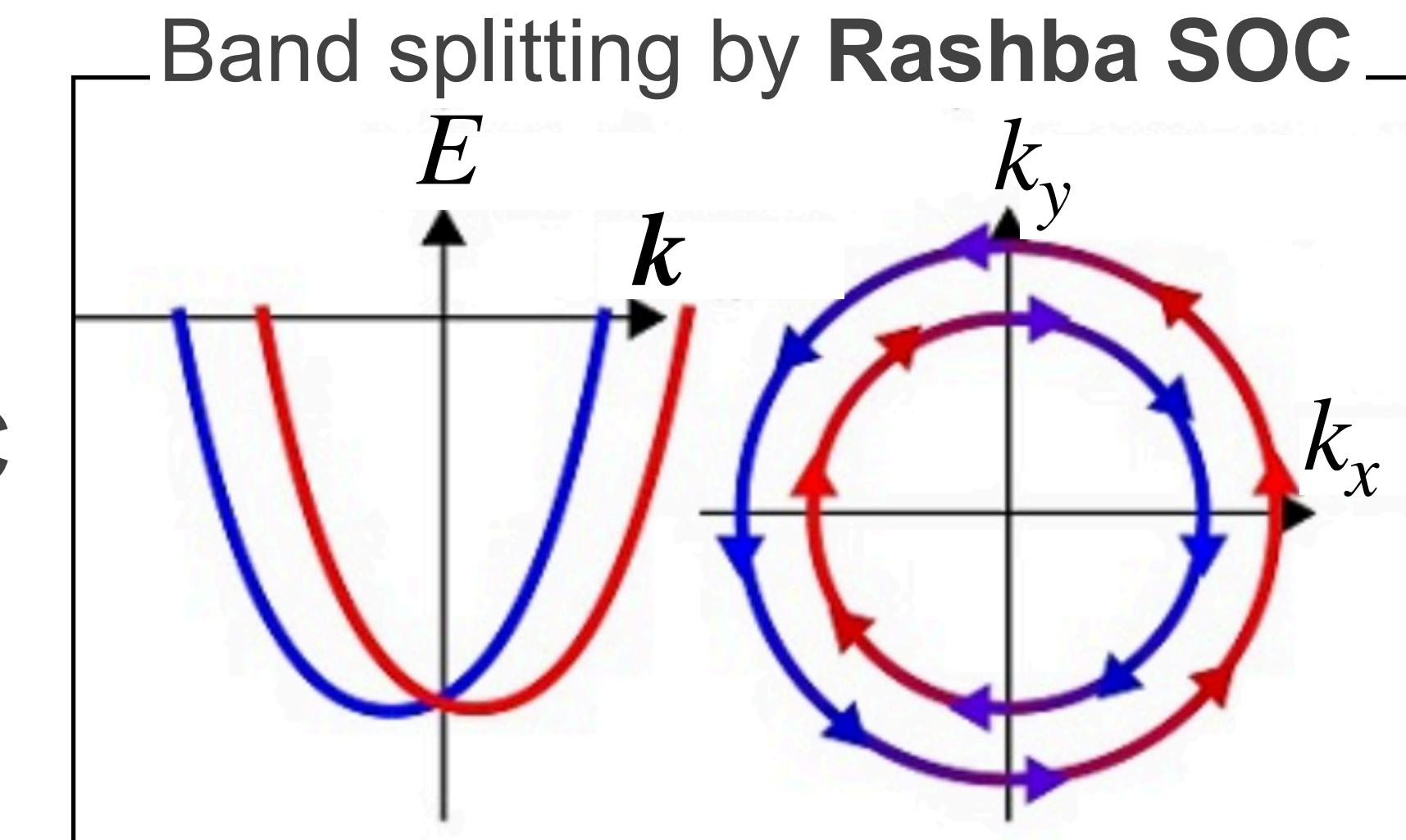
Investigation of
the contribution of **Rashba SOC**
to **spin current generation**
in **Janus TMDCs**

Spin polarized perpendicular in the plane of the electron momentum direction

Example: Free electron systems



Rashba SOC

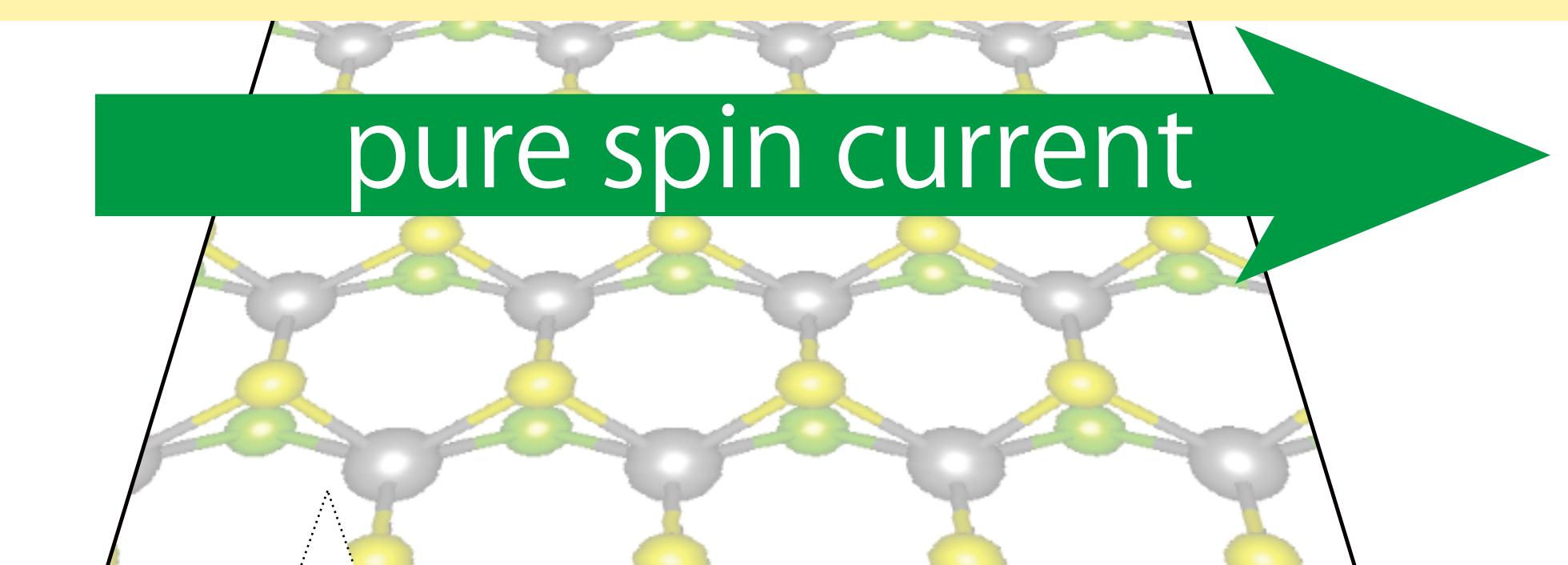


Key findings

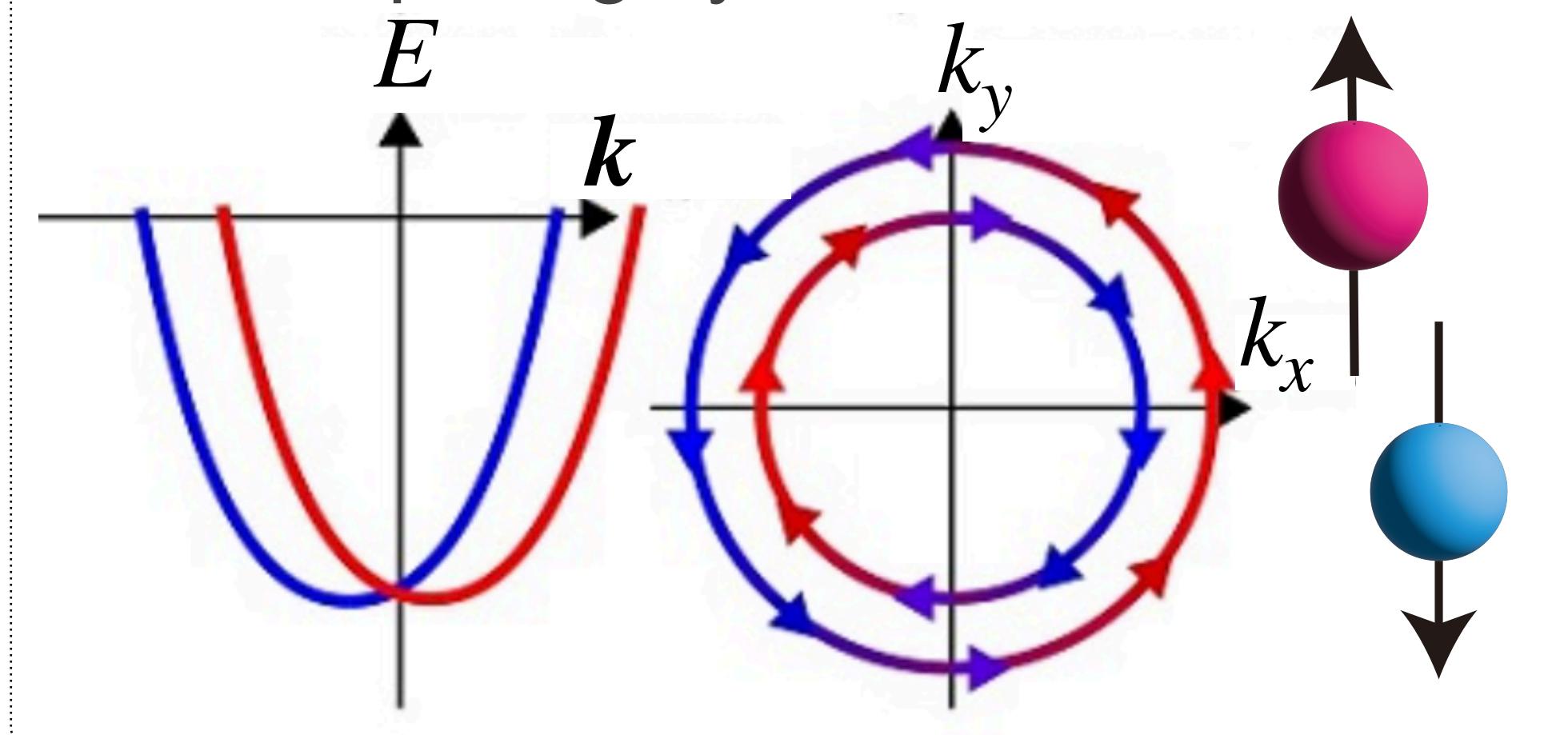
There is a **optically-induced pure spin current**
in the Janus TMDC that is induced by the **Rashba SOC**

Thesis of study

Janus TMDC is a candidate
for **optospintrronics devices**



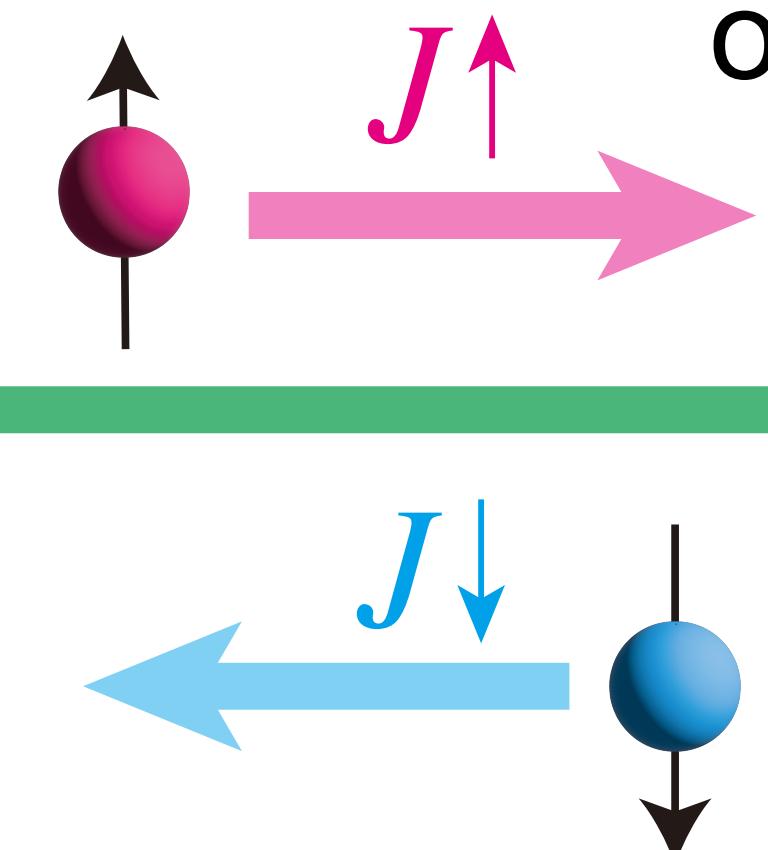
Band splitting by Rashba SOC



pure spin current

Flow of the spin angular momentum

only without flow of the charge



optically-induced

- Electric field induced by light

Step① Tight-binding model

- Rashba SOC parameter
- Energy band structure
- Spin polarization

Step② Spin dependent optical hall conductivity

- Kubo formula
- Evaluation

Spin dependent optical hall conductivity

Spin current generation efficiency
(spin Hall angle)

Step③ Symmetry analysis

- Neumann's principle

Multi-orbital TB model and Rashba SOC parameter

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Considering $d_{z^2}, d_{xy}, d_{x^2-y^2}$ orbitals of transition metal atom

$$\hat{H}(\mathbf{k}) = \boxed{\hat{\sigma}_0 \otimes \hat{H}_{TNN}(\mathbf{k}) + \hat{\sigma}_z \otimes \frac{1}{2} \lambda \hat{L}_z} + \boxed{\hat{H}_R(\mathbf{k})}$$

Common to TMDC

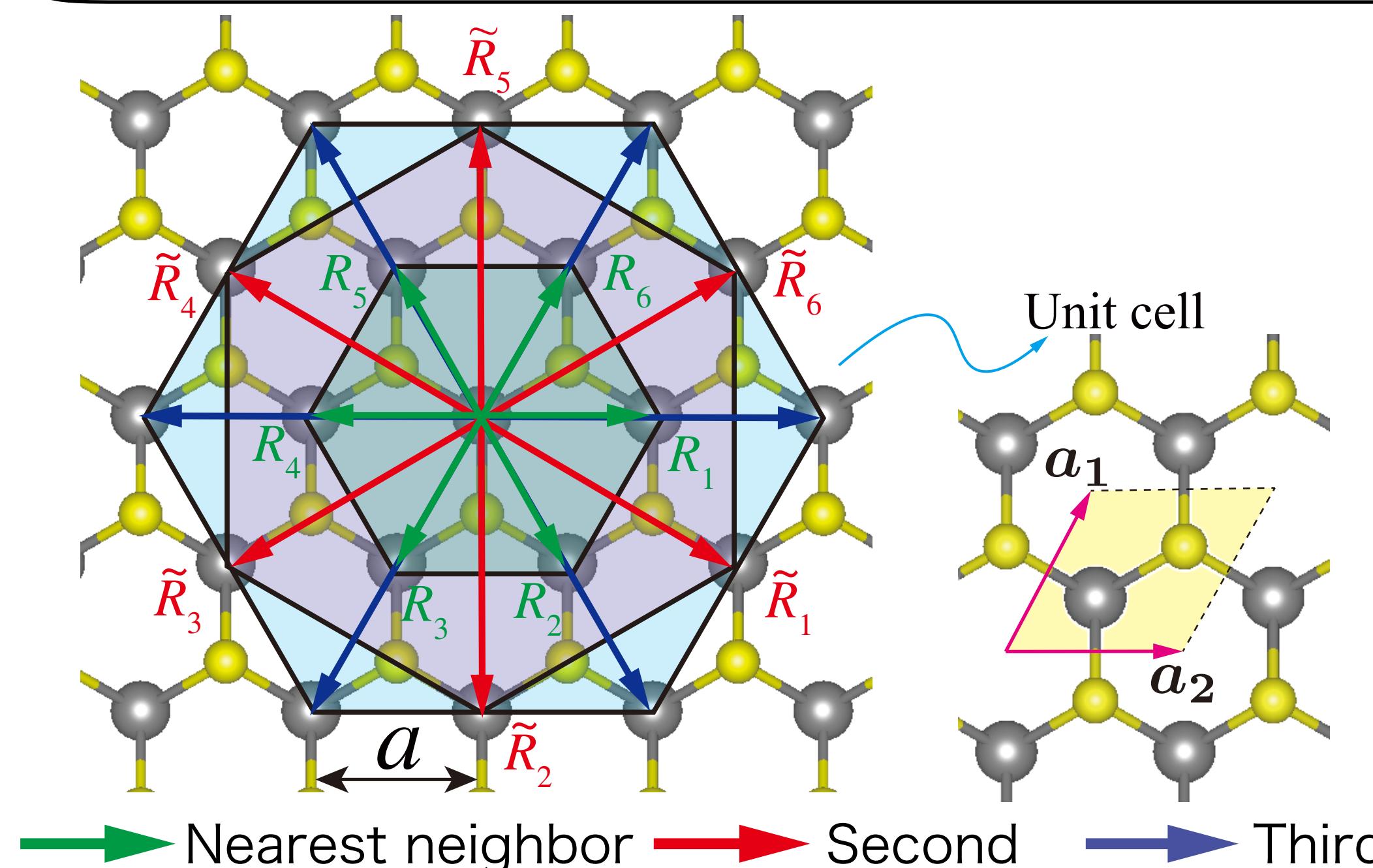
Non-SOC term Ising SOC term Rashba SOC term

$$\hat{H}_R = (f_x(\mathbf{k})\hat{\sigma}_y - f_y(\mathbf{k})\hat{\sigma}_x) \otimes \text{diag}(2\alpha_0, 0, 0)$$

$$f_x(\mathbf{k}) = \sin(2\alpha) + \sin(\alpha)\cos(\beta),$$

$$f_y(\mathbf{k}) = \sqrt{3}\sin(\beta)\cos(\alpha).$$

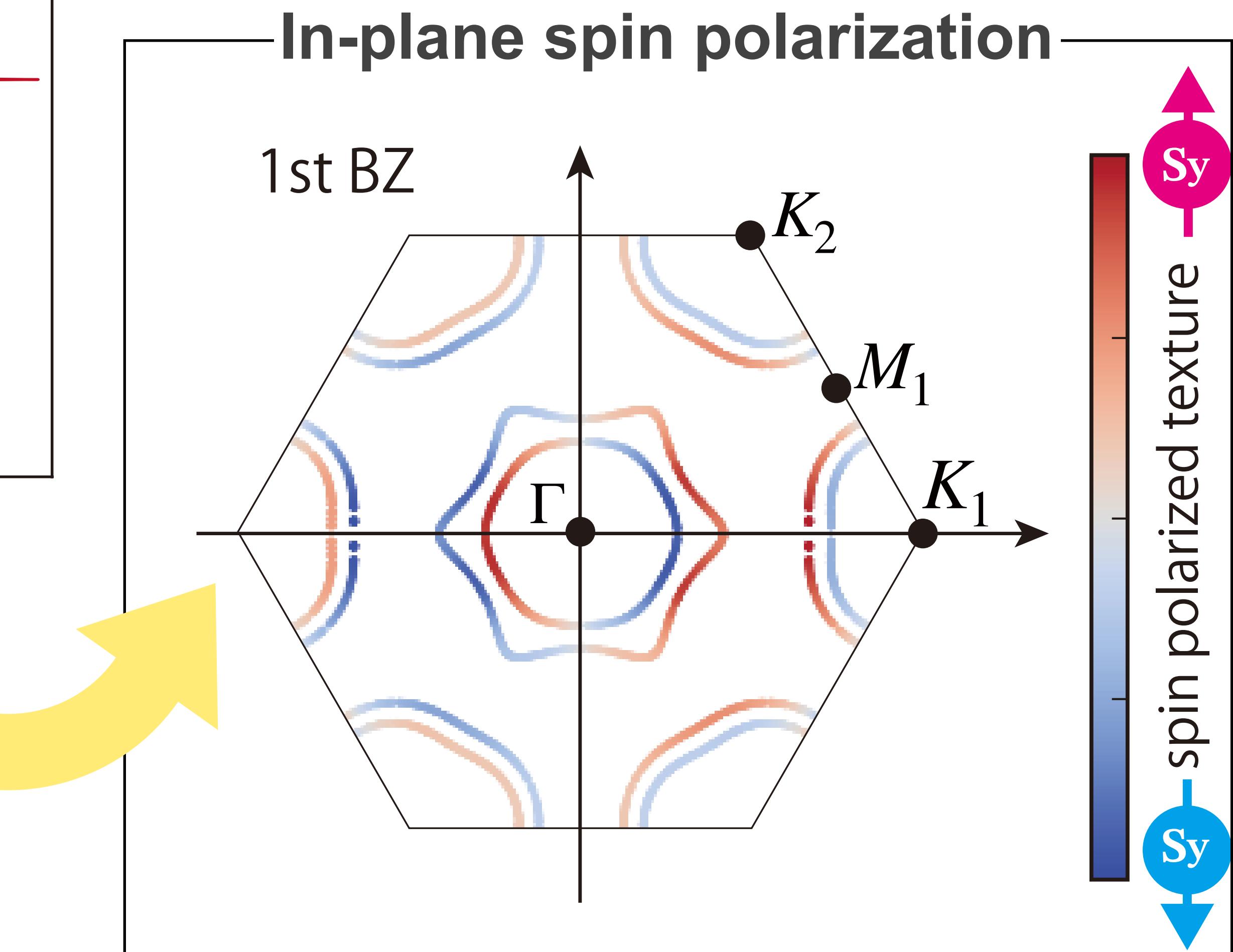
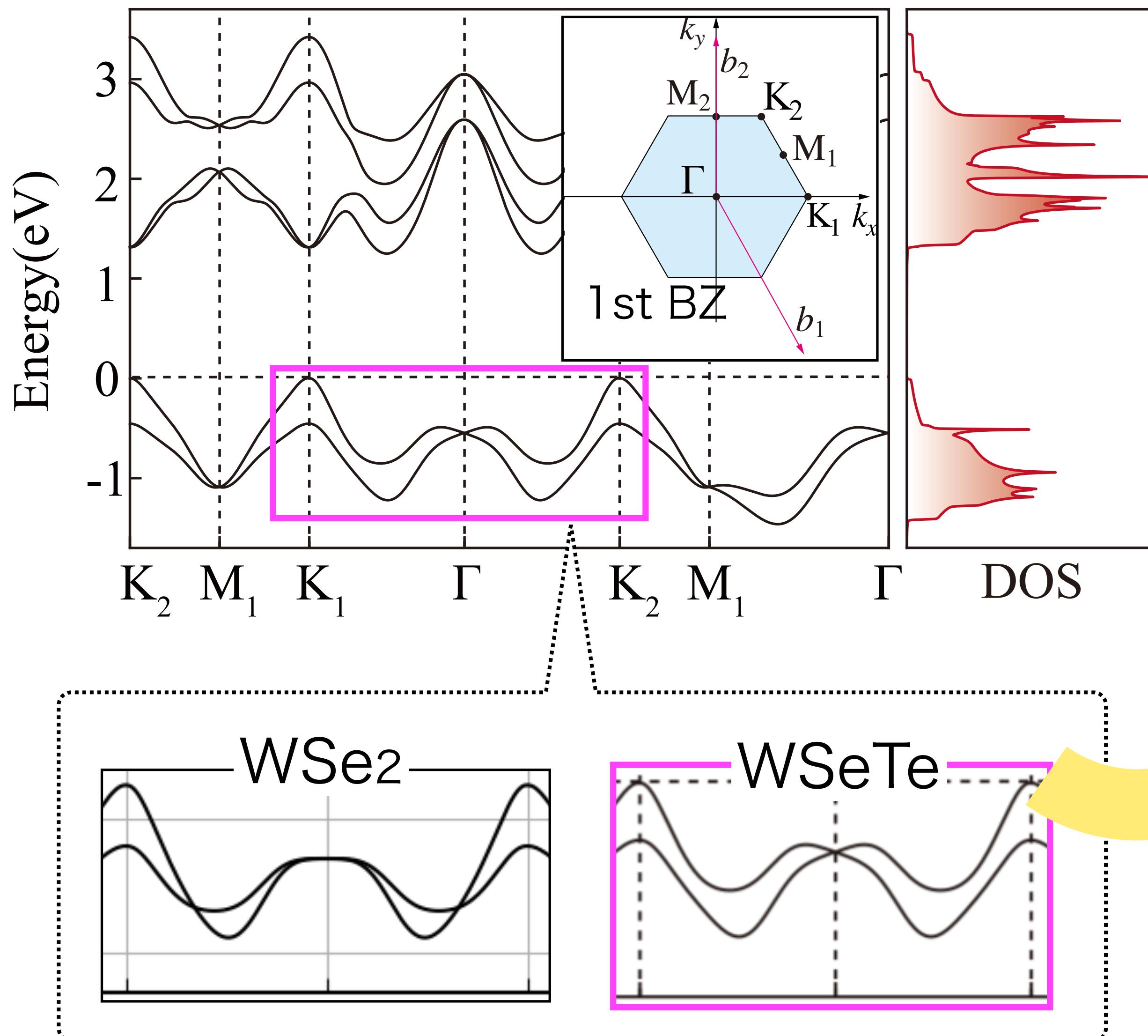
$$(\alpha, \beta) = (\frac{1}{2}k_x a, \frac{\sqrt{3}}{2}k_y a)$$



● Rashba SOC parameter α_0

- Determining the intensity of band splitting
- Setting $\alpha_0 = 0.045$ eV
, which corresponds to **WSeTe**

Energy band structure and spin polarization of WSeTe



- Rashba SOC-derived band splitting occurs near the Γ point

Spin dependent optical hall conductivity

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$$\sigma_{ij}^{spin(k)}(\omega) = \frac{i\hbar e}{(2\pi)^2} \int_{BZ} d^2k \sum_{n \neq m} \frac{f(E_n(\mathbf{k})) - f(E_m(\mathbf{k}))}{E_m(\mathbf{k}) - E_n(\mathbf{k})} \times \frac{\langle u_n(\mathbf{k}) | \hat{j}_i^{spin(k)} | u_m(\mathbf{k}) \rangle \langle u_m(\mathbf{k}) | \hat{v}_j | u_n(\mathbf{k}) \rangle}{E_m(\mathbf{k}) - E_n(\mathbf{k}) - \hbar\omega - i\eta}$$

Spin Hall Angle

$$\theta^{spin} = \frac{2e}{\hbar} \frac{\sigma_{xy}^{spin}}{\sigma_{xx}}$$

Calculated from TBM

$E_n(\mathbf{k})$: Energy eigenvalue n -band

$|u_n(\mathbf{k})\rangle$: Energy eigenstate n -band

$\hat{v}_i = \frac{1}{\hbar} \frac{\partial \hat{H}(\mathbf{k})}{\partial k_i}$: Velocity operator

$\hat{j}_i^{spin(z)} = \frac{1}{2} \{\hat{\sigma}_z, \hat{v}_i\}$: Spin current density operator

variable value

ω : optical angular frequency

i : Spin current conduction direction
 j : Photoelectric field oscillation direction

$spin(k)$: Spin polarization direction

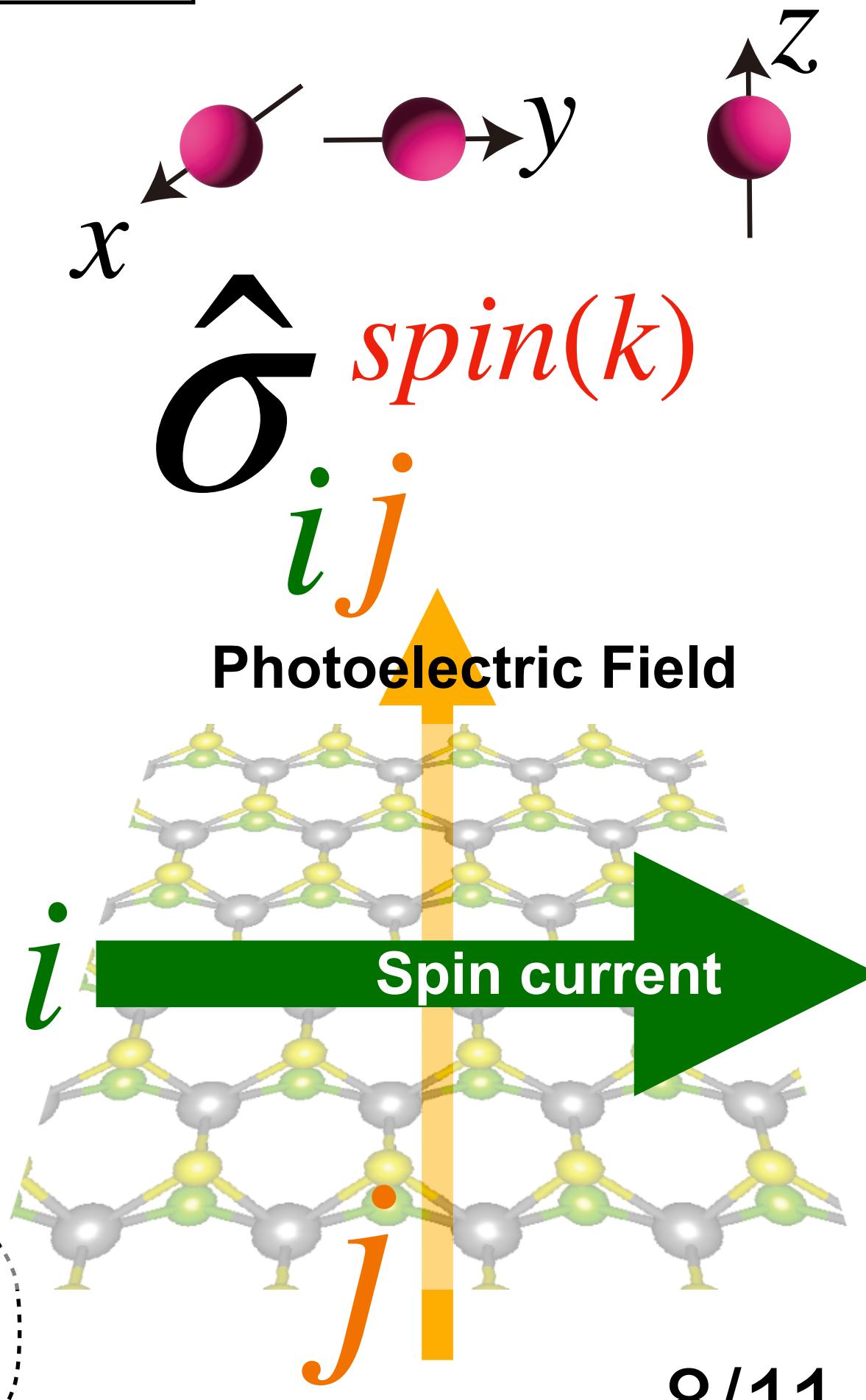
**Experimental conditions
and external parameters**

Other symbols

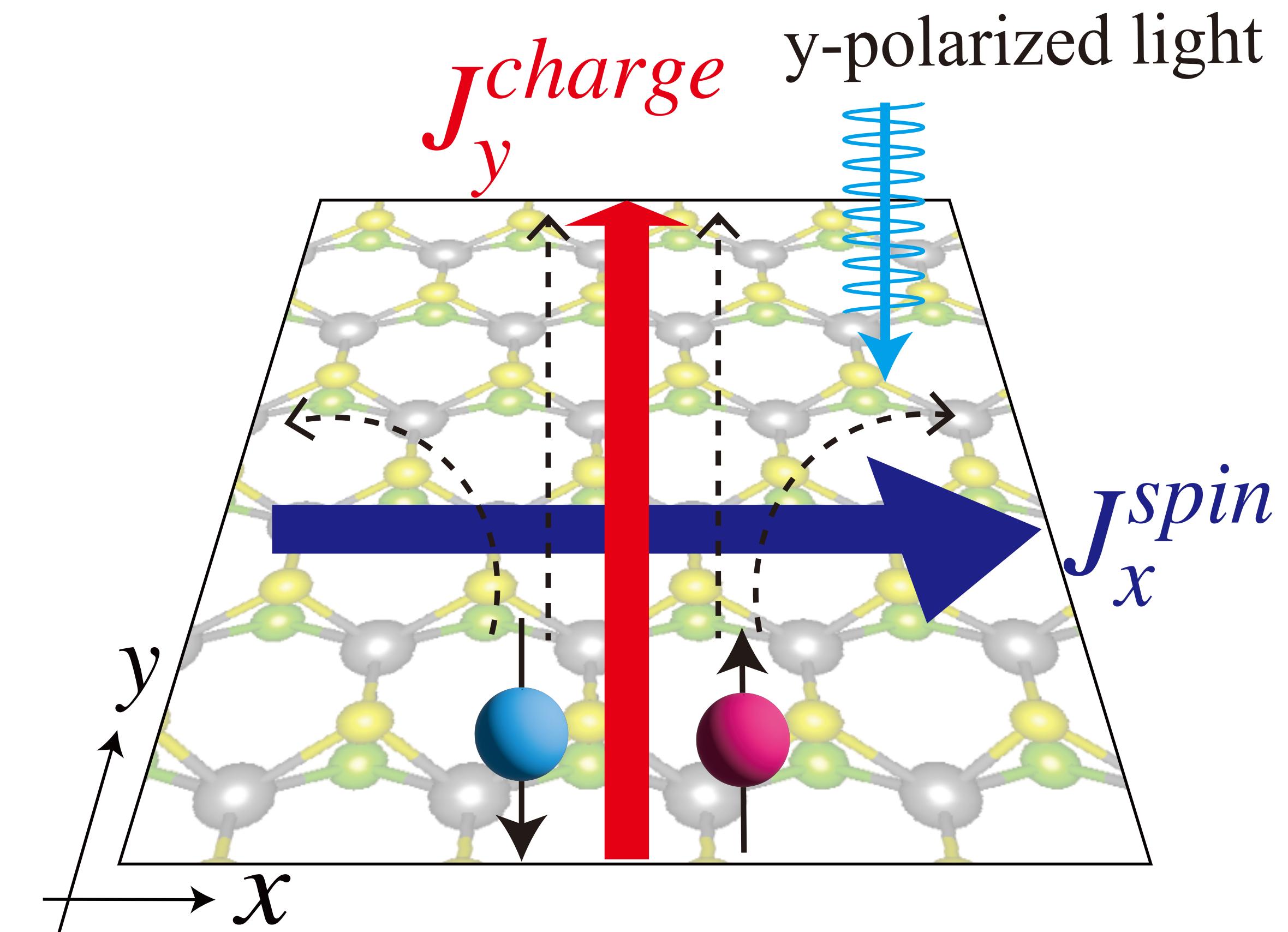
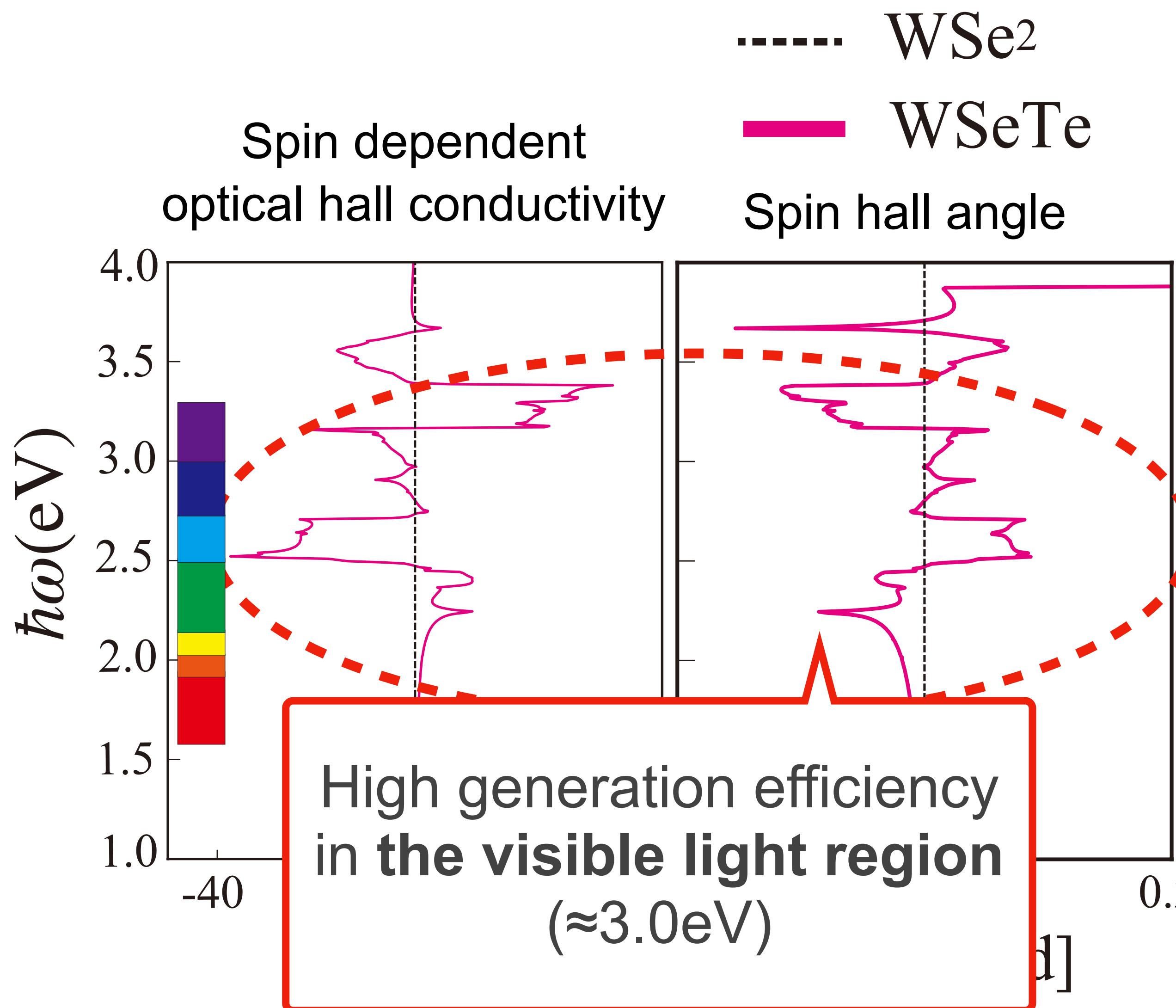
η : an infinitesimally small real number

$\hat{\sigma}_z$: Pauli matrix
(z-component)

$f(E_n(\mathbf{k}))$: Fermi distribution function



Optically induced pure spin current



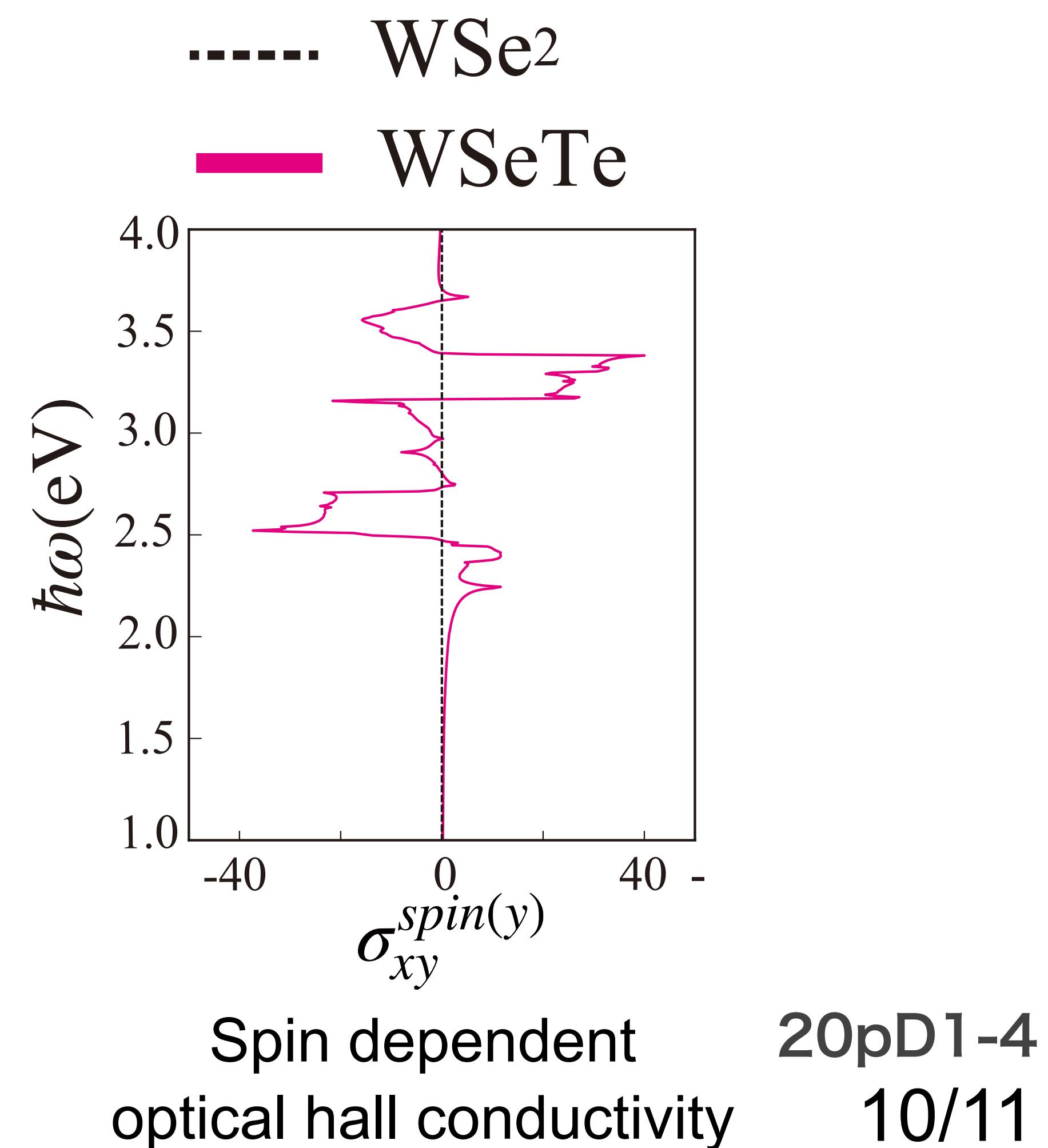
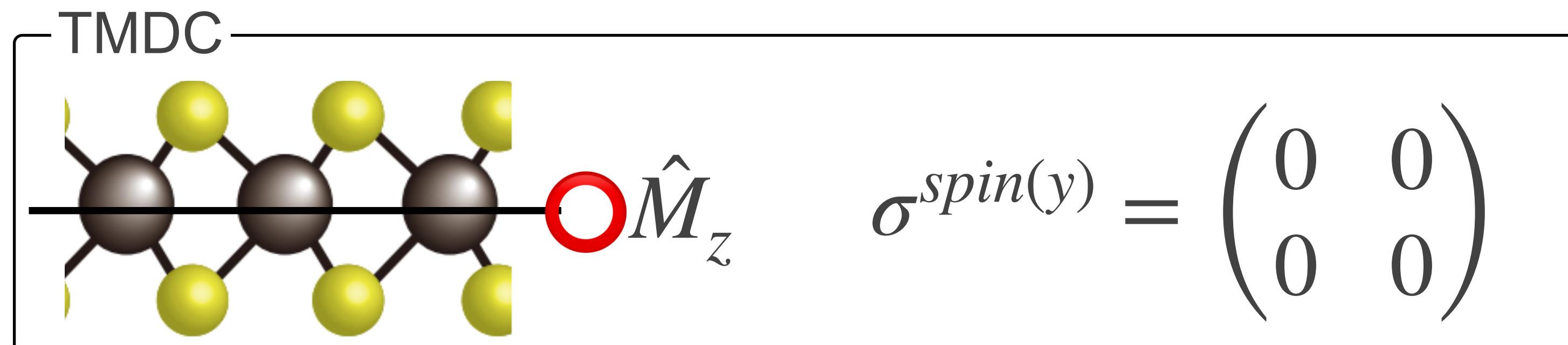
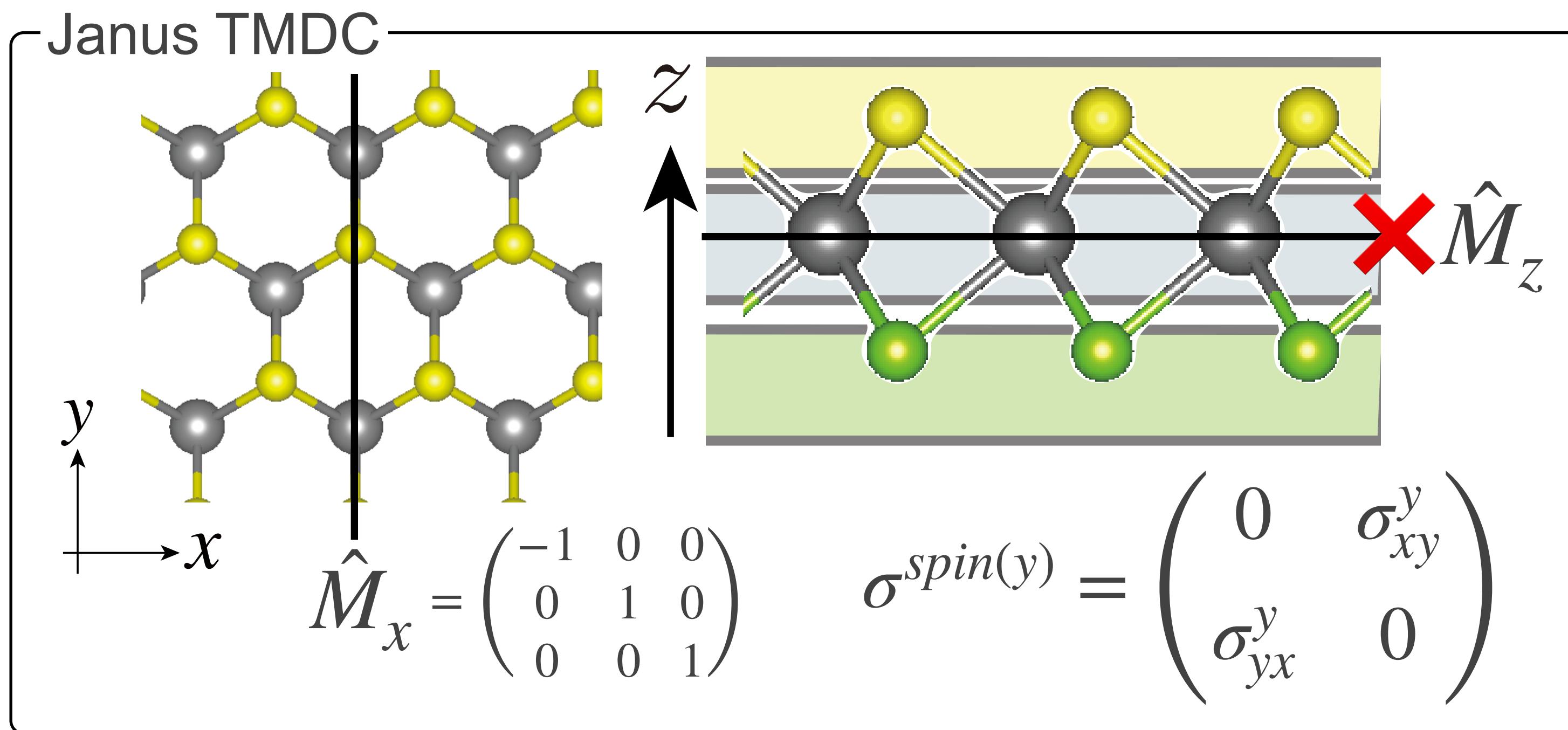
- Pure spin currents are generated

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Neumann's principle

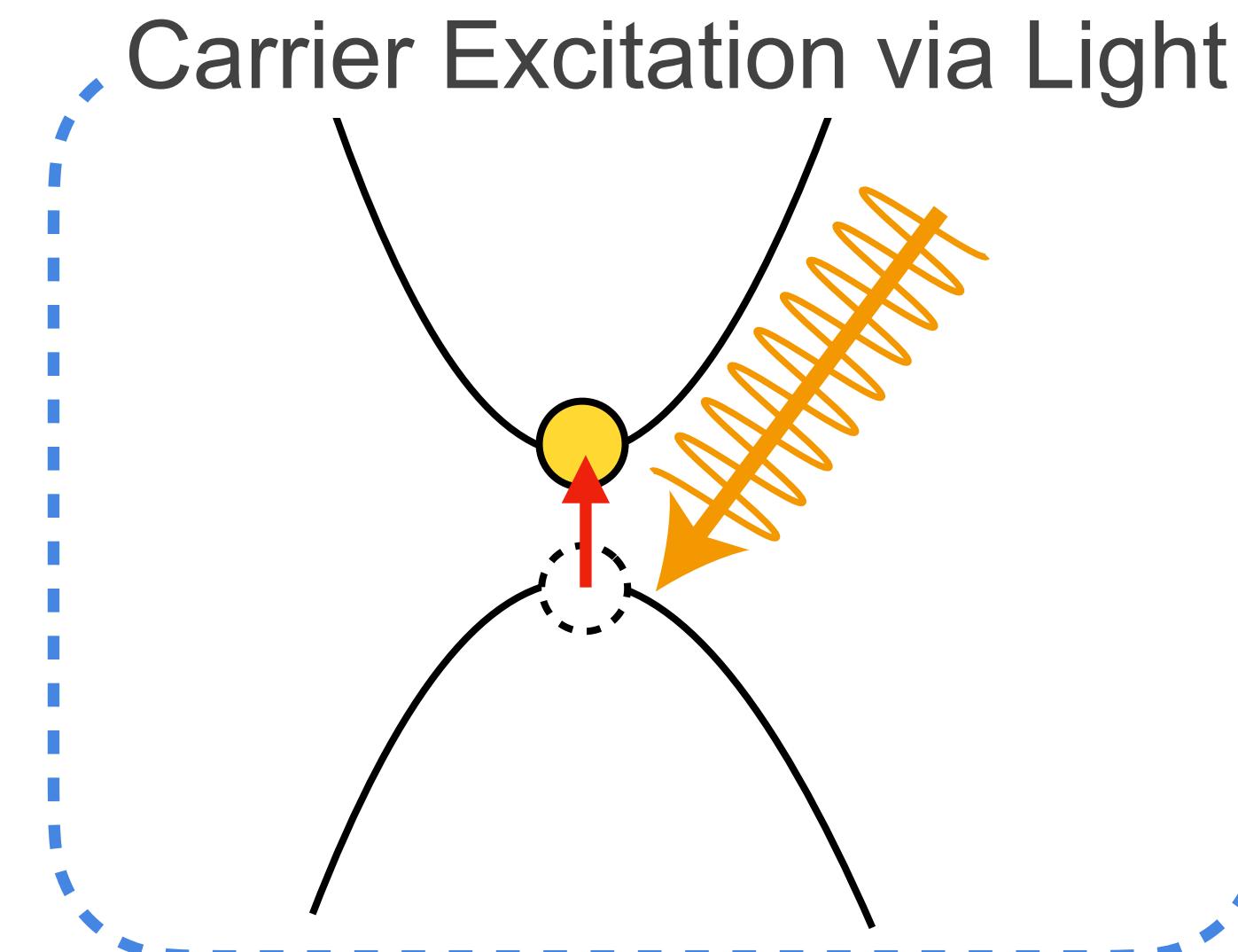
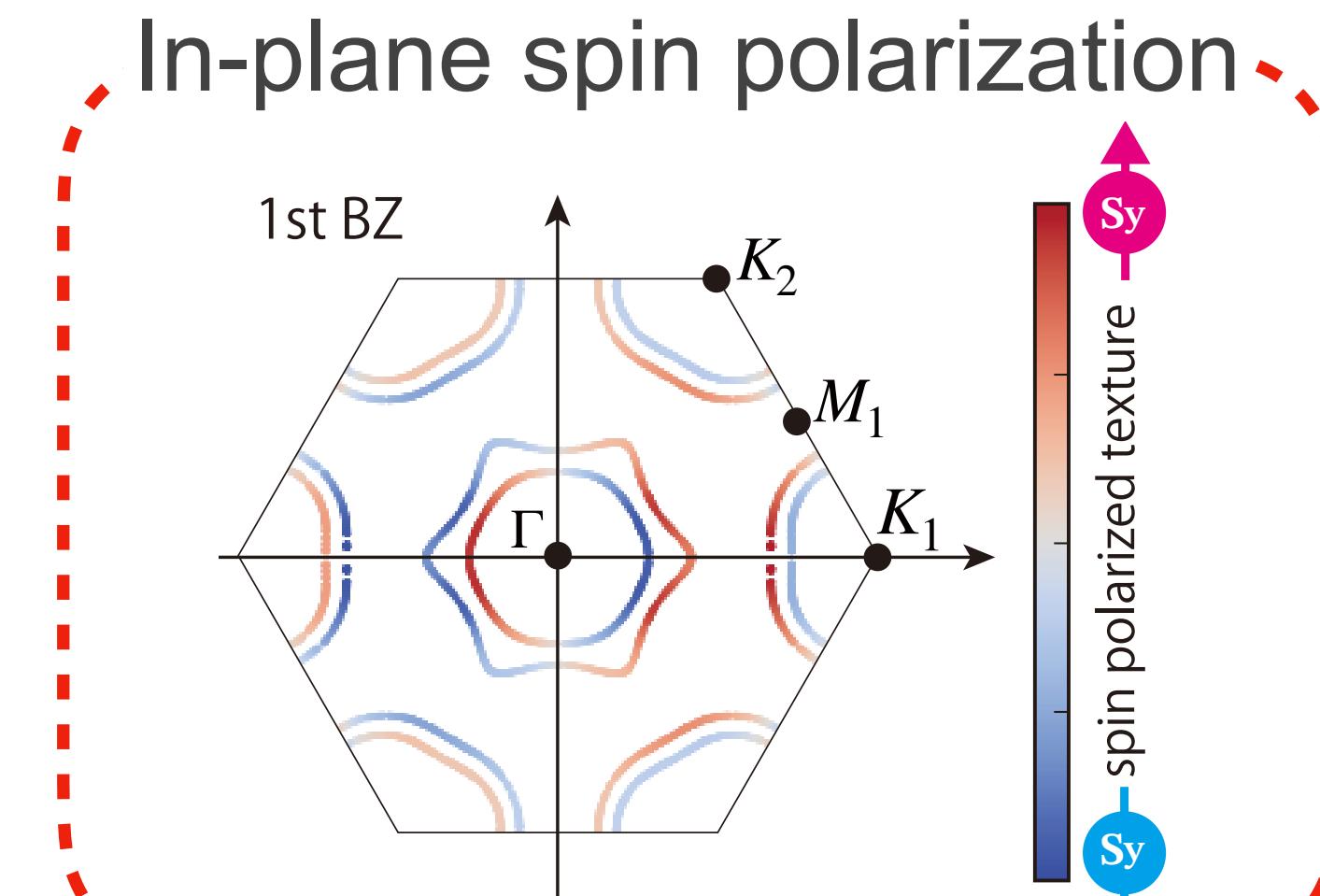
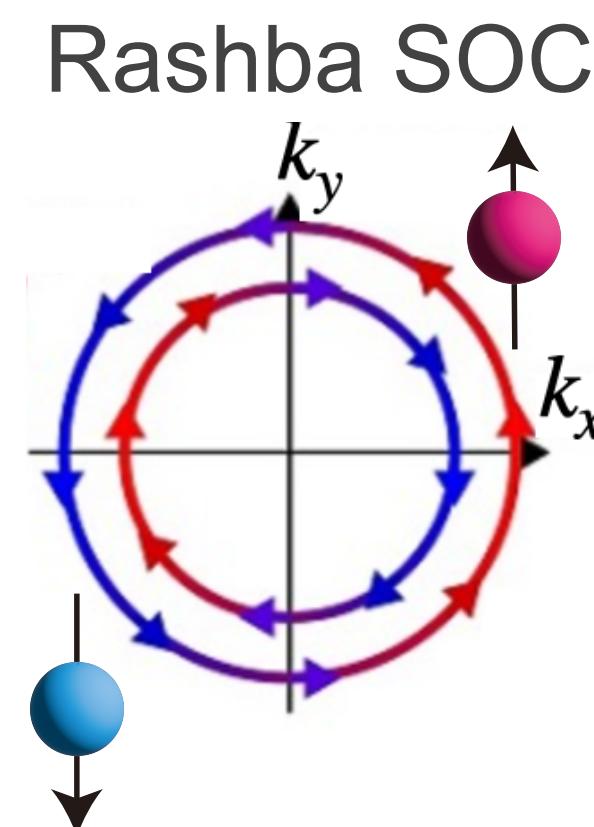
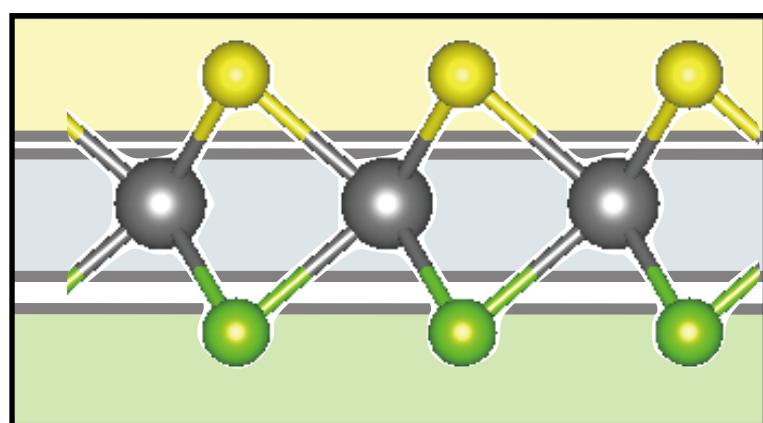
The physical properties of a crystal must obey the symmetry of its structure

$$\sigma_{\beta\gamma}^{\alpha} = \det(R)R_{\alpha\alpha'}R_{\beta\beta'}R_{\gamma\gamma'}\sigma_{\beta'\gamma'}^{\alpha'} \quad \hat{R} \text{ Symmetry operator} \quad \det(R) = \pm 1$$



Factors

Structural
asymmetry

Methods

Step①

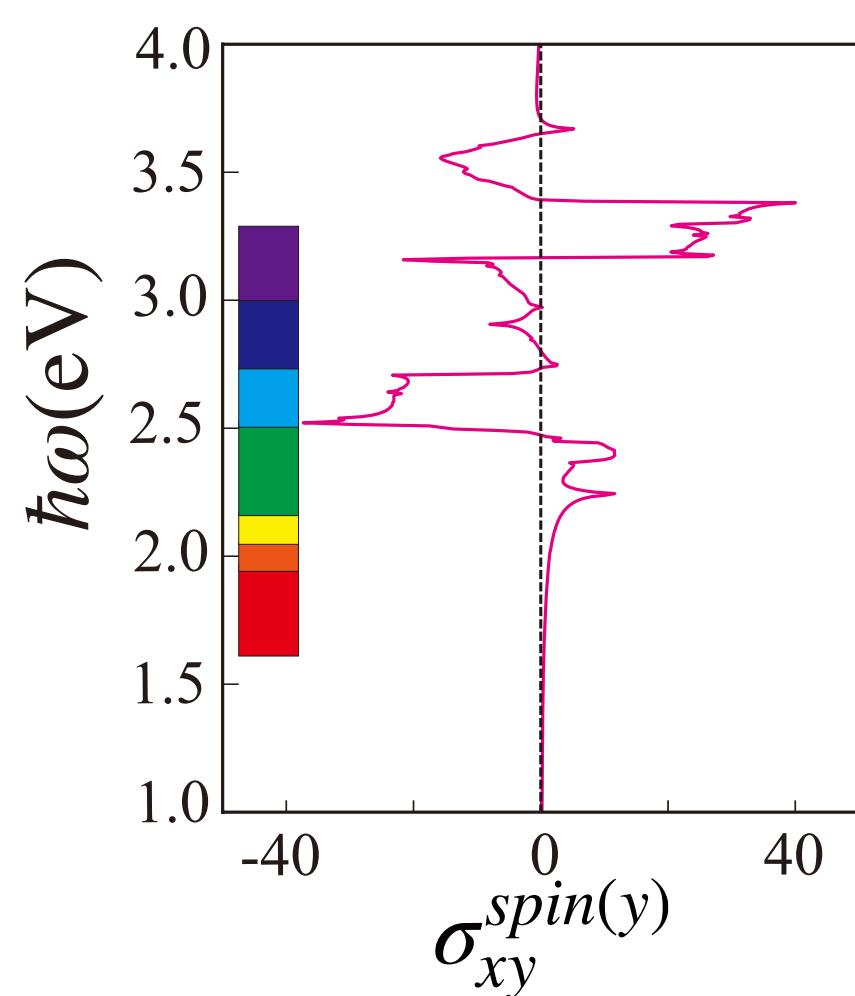
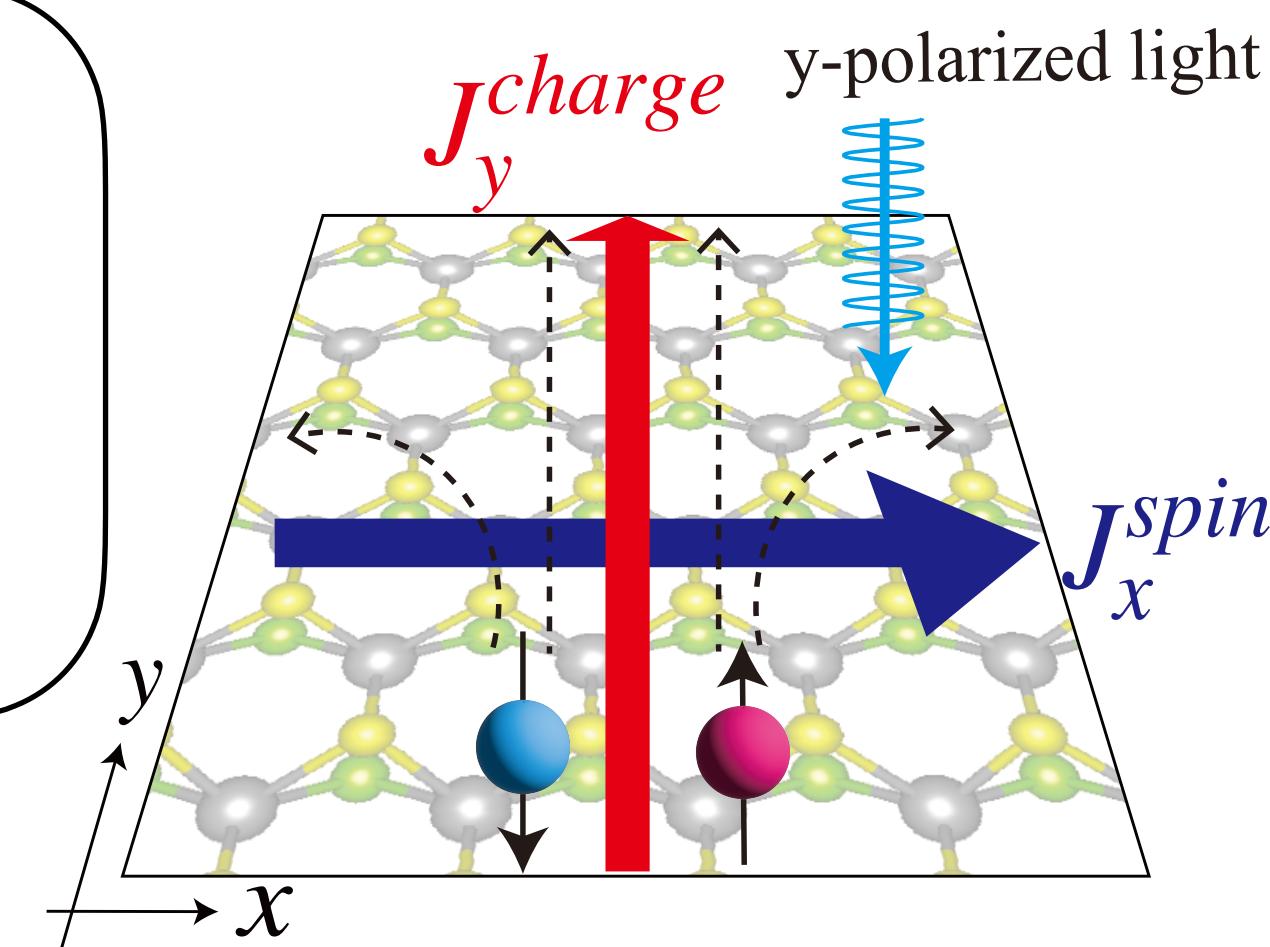
Tight-binding model

Step②

Spin dependent optical hall conductivity

Step③

Neumann's principle



Our results offer a new degree of freedom

for designing optospintronic devices, such as **spin current harvesting** via light irradiation in 2D materials

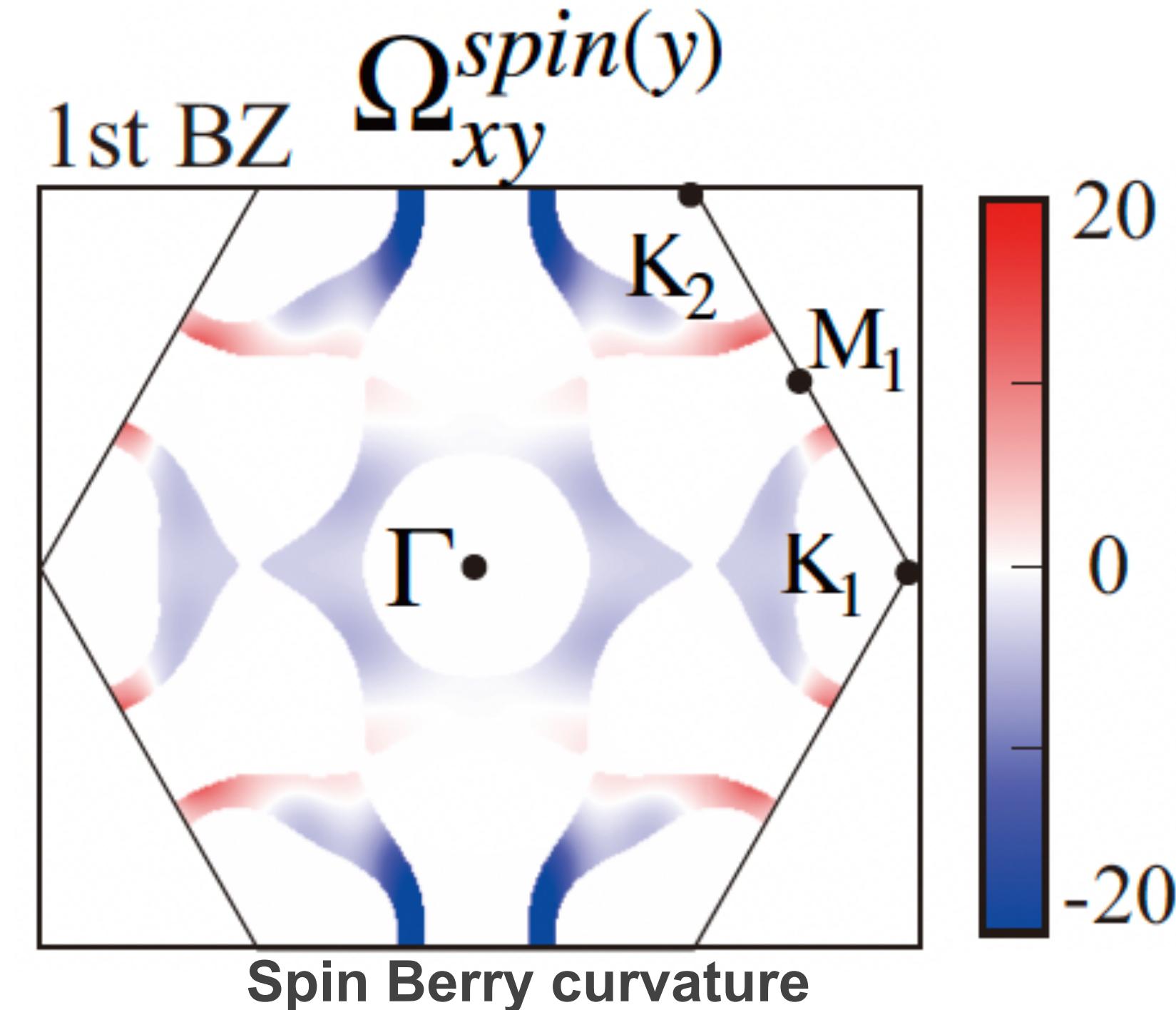
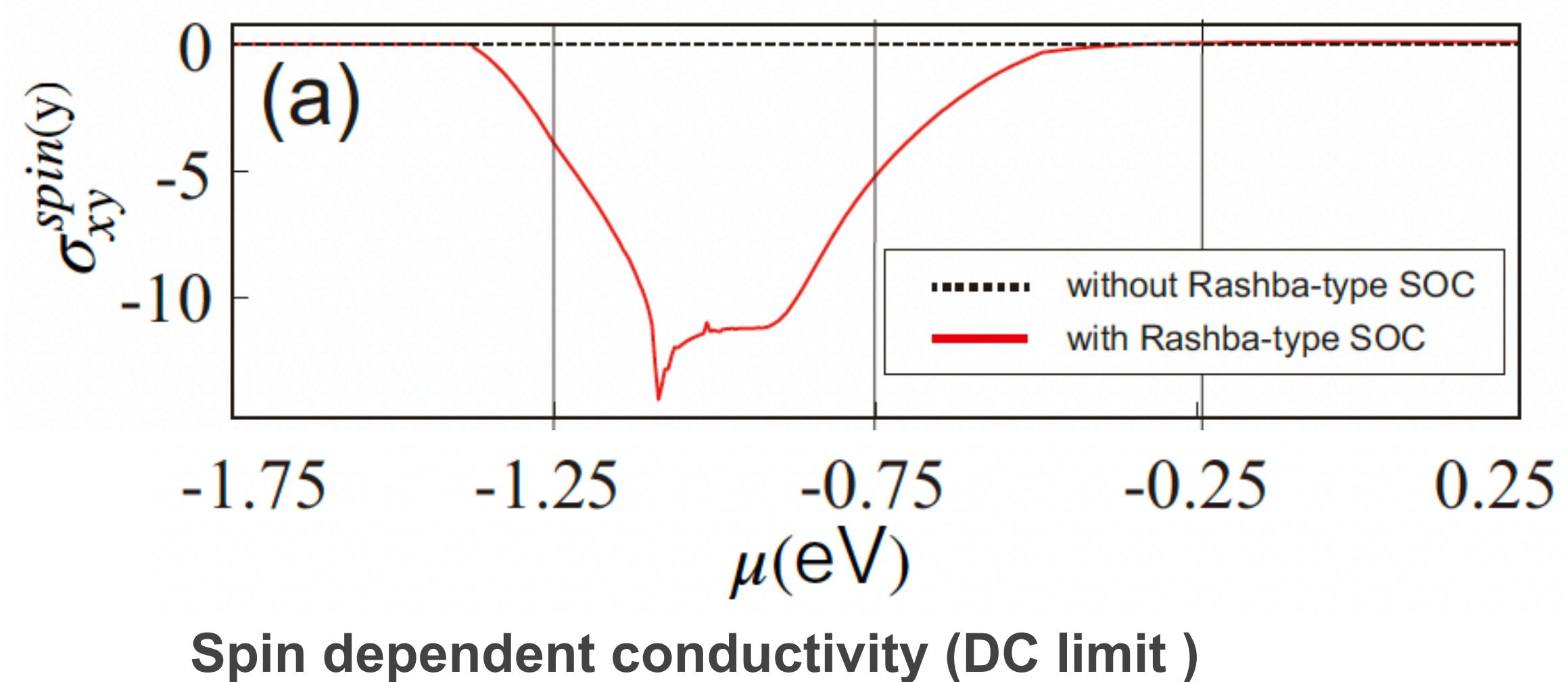
Appendix Direct current limit

$$\sigma_{ij}^{\text{spin}(k)}(\omega) = \frac{e}{(2\pi)^2} \int_{\text{BZ}} \Omega_{ij}^{\text{spin}(k)}(\omega, \mathbf{k}) d^2\mathbf{k}$$

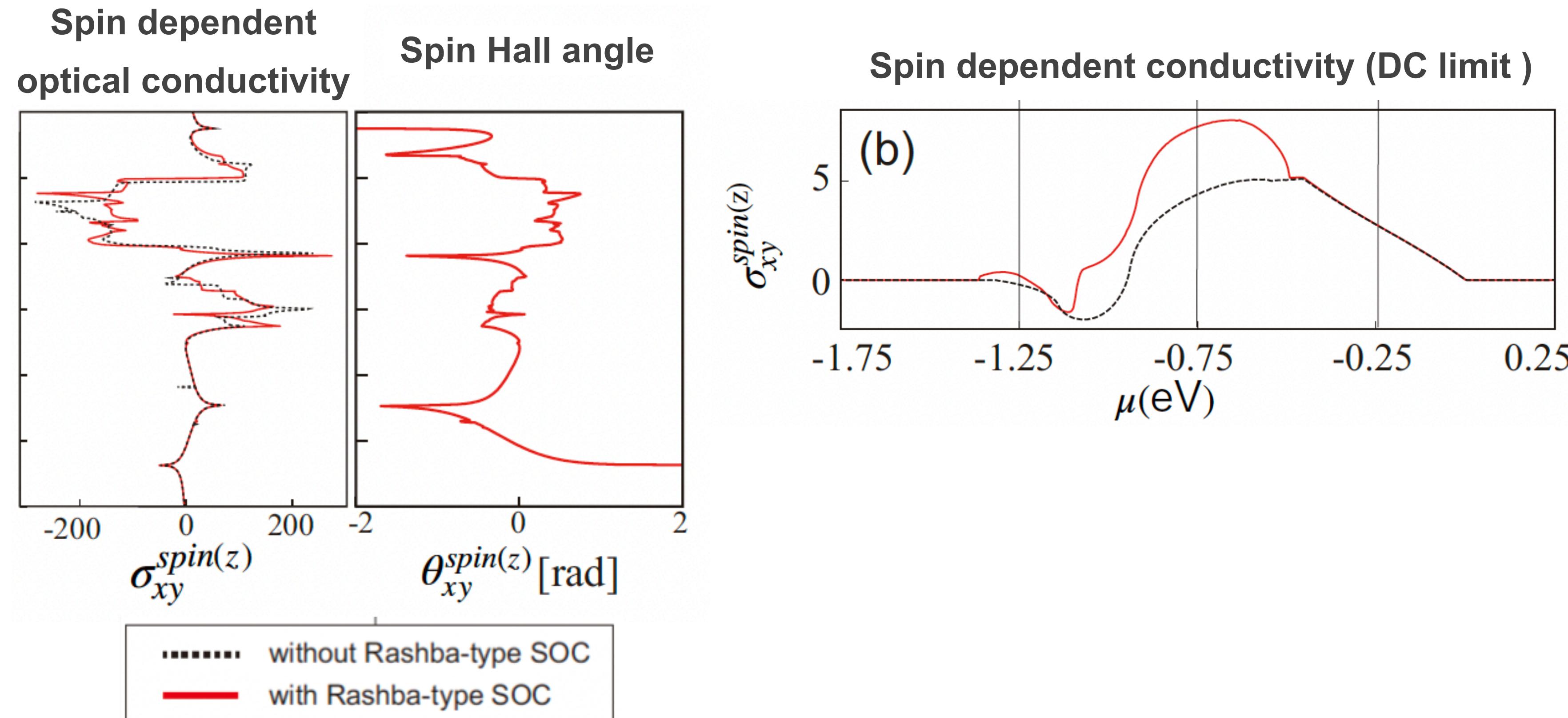
$\omega = 0$

Spin Berry curvature

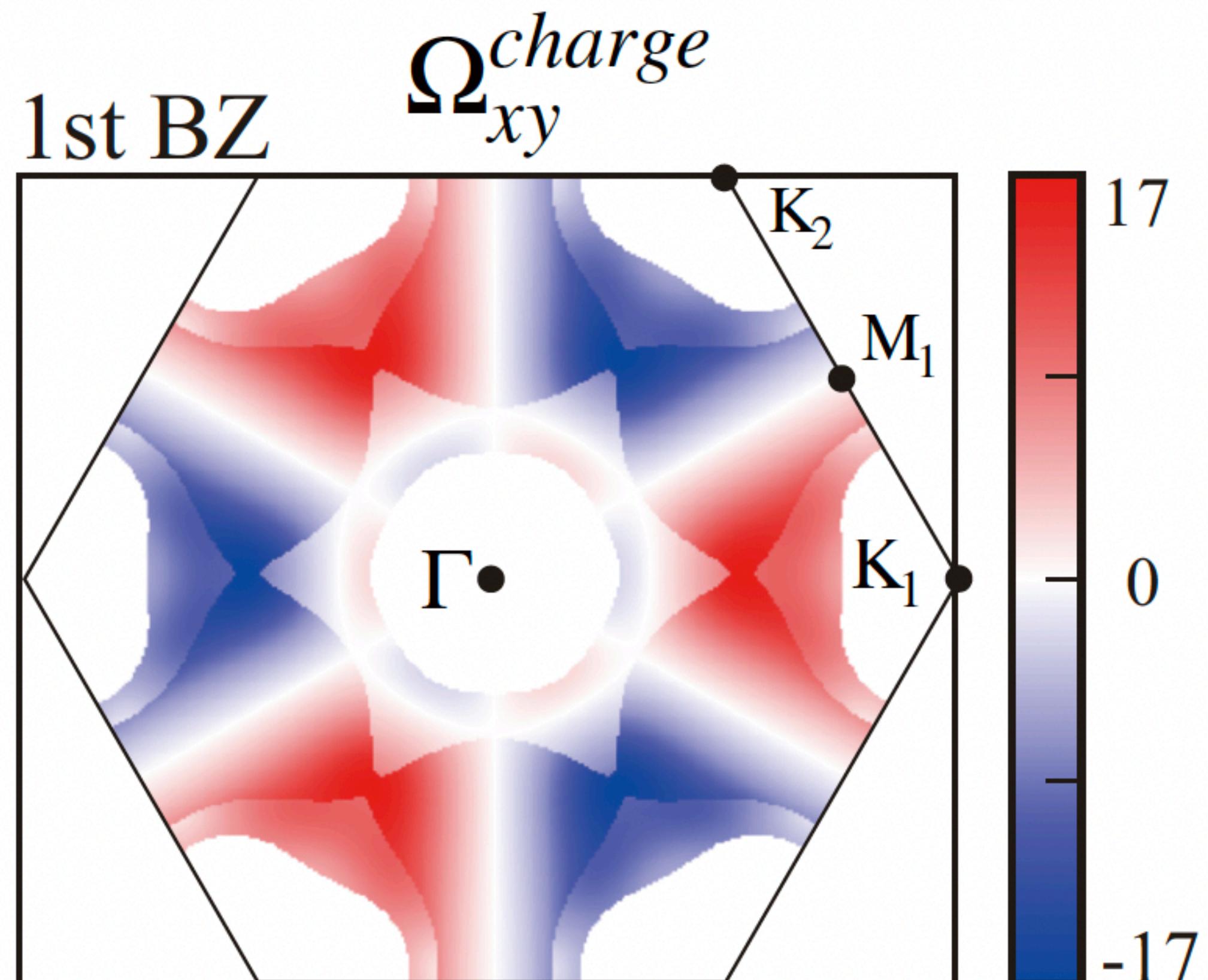
$$\Omega_{i\perp j}^{\text{spin}(k)}(\mathbf{k}) = \hbar \sum_n f(E_n(\mathbf{k})) \sum_{m(\neq n)} \frac{-2\text{Im}\langle u_n(\mathbf{k}) | \hat{j}_i^{\text{spin}(k)} | u_m(\mathbf{k}) \rangle \langle u_m(\mathbf{k}) | \hat{v}_j | u_n(\mathbf{k}) \rangle}{(E_m(\mathbf{k}) - E_n(\mathbf{k}))^2}$$



Appendix Ising SOC derived pure spin current



Appendix Charge Hall current



Appendix

Neumann's principle

可視光のエネルギーと色は、波長によって異なります。 

紫：エネルギーが高い (380~450nm、2.755~3.26eV) 

青：エネルギーが高い (430~490nm) 

緑：エネルギーが低い (495~570nm、2.175~2.50eV) 

黄：エネルギーが低い (570~590nm、2.10~2.175eV) 

橙：エネルギーが低い (590~620nm、1.99~2.10eV) 

赤：エネルギーが最も低い (620~750nm、1.65~1.99eV) 